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Handa et al. (43) **Pub. Date: Dec. 8, 2022**(54) **LOW OFF-LEAKAGE CURRENT SWITCH****Publication Classification**(71) Applicant: **Analog Devices, Inc.**, Wilmington, MA (US)(51) **Int. Cl.**
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(57) **ABSTRACT**

Low-leakage switch circuit techniques to reduce leakage current of an off-state switch, while maintaining a low on-resistance. The low-leakage switch circuit may allow measurement of low current signals in a transimpedance amplifier with improved accuracy without, the need for calibration. The low-leakage switch circuit may include a bootstrapping path connecting two or more terminals or voltage nodes of an off-state switch in the switch circuit. The bootstrapping path is configured to bootstrap major leakage current contributors in the switch circuit, such as the substrate diode leakage, the subthreshold leakage, or combinations thereof.

